

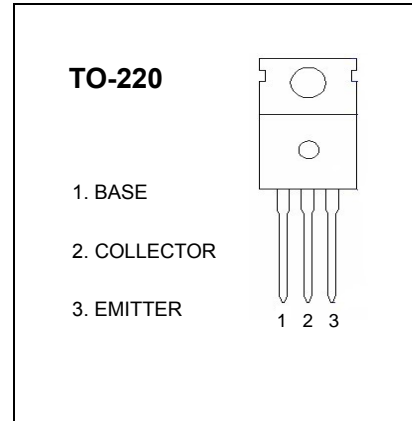
TO-220 Plastic-Encapsulate Transistors

2SA940 TRANSISTOR (PNP)

FEATURES

- Wide Safe Operating Area.
- Complementary to 2SC2703

MAXIMUM RATINGS (T_a=25°C unless otherwise noted)



Symbol	Parameter	Value	Unit
V _{CB0}	Collector-Base Voltage	-150	V
V _{CEO}	Collector-Emitter Voltage	-150	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current -Continuous	-1.5	A
P _C	Collector Power Dissipation	1.5	W
T _j	Junction Temperature	150	°C
T _{stg}	Storage Temperature Range	-55-150	°C

ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = -100μA, I _E = 0	-150			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C = -1mA, I _B = 0	-150			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E = -100μA, I _C = 0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} = -120V, I _E = 0			-10	μA
Emitter cut-off current	I _{EBO}	V _{EB} = -5V, I _C = 0			-10	μA
DC current gain	h _{FE}	V _{CE} = -10V, I _C = -0.5A	40		140	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = -0.5A, I _B = -50mA			-1.5	V
Base-emitter voltage	V _{BE}	V _{CE} = -10V, I _C = -0.5A	-0.65		-0.85	V
Transition frequency	f _T	V _{CE} = -10V, I _C = -0.5A		4		MHz
Collector output capacitance	C _{ob}	V _{CB} = -10V, I _E = 0, f = 1MHz		55		pF